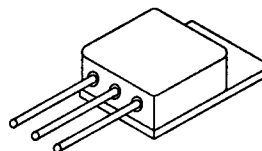
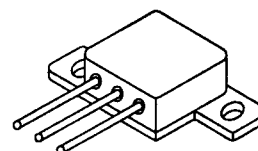




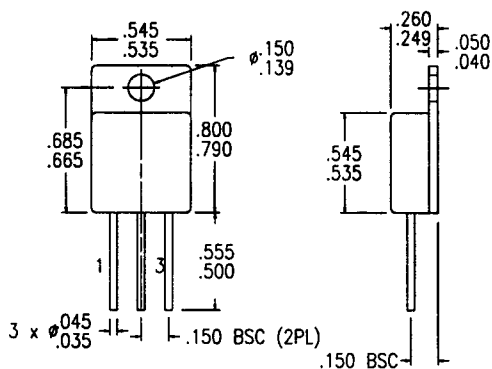
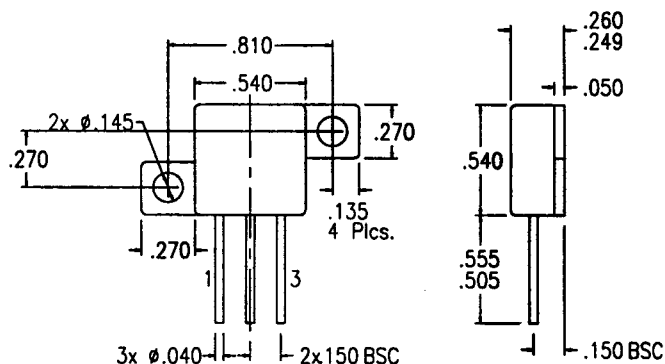
PRELIMINARY

SOLID STATE DEVICES, INC14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**Designer's Data Sheet****FEATURES:**

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed package
- Ceramic seals for improved hermeticity
- TX, TXV and Space Level screening available
- Replaces: IRFM230 Types

**SFF230M
SFF230Z****9 AMP
200 VOLTS
0.40Ω
N-CHANNEL
POWER MOSFET****TO-254****TO-254Z****MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	200	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	9	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	2	°C/W
Total Device Dissipation @ TC=25°C Total Device Dissipation @ TC=55°C	P _D	63 48	Watts

PACKAGE OUTLINE: TO-254**PIN OUT:****PIN 1: DRAIN****PIN 2: SOURCE****PIN 3: GATE****PACKAGE OUTLINE: TO-254Z****PIN OUT:****PIN 1: DRAIN****PIN 2: SOURCE****PIN 3: GATE**

Available with Glass or Ceramic Seals. Contact Factory for details.

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.**DATA SHEET #: F00015 C****MED**

SFF230M SFF230Z

PRELIMINARY



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ELECTRICAL CHARACTERISTICS @ $T_J=25^{\circ}\text{C}$ (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage ($V_{GS}=0\text{ V}$, $I_D=250\mu\text{A}$)		BV_{DSS}	200	---	---	V
Drain to Source on State Resistance ($V_{GS}=10\text{ V}$, $I_D=5\text{ A}$)		$R_{DS(on)}$	---	0.25	0.4	Ω
On State Drain Current ($V_{DS}>I_D(on) \times R_{DS(on)}$ Max, $V_{GS}=10\text{ V}$)		$I_D(on)$	9	---	---	A
Gate Threshold Voltage ($V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$)		$V_{GS(th)}$	2	---	4	V
Forward Transconductance ($V_{DS}>I_D(on) \times R_{DS(on)}$ Max, $I_{DS}=5\text{ A}$)		g_{fs}	3.0	6	---	S(Ω)
Zero Gate Voltage Drain Current ($V_{DS}=\text{max rated voltage}$, $V_{GS}=0\text{ V}$) ($V_{DS}=80\%$ rated V_{DS} , $V_{GS}=0\text{ V}$, $T_A=125^{\circ}\text{C}$)		I_{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V_{GS}	I_{GSS}	---	---	100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	$V_{GS}=10\text{ Volts}$ 80% rated V_{DS} $I_D=12\text{ A}$	Q_g Q_{gs} Q_{gd}	---	30 10 9	39 ---	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	$V_{DD}=50\%$ rated V_{DS} 50% rated I_D $R_G=15\Omega$	$t_{d(on)}$ t_r $t_{d(off)}$ t_f	---	---	30 50 50 40	nsec
Diode Forward Voltage ($I_S=\text{rated } I_D$, $V_{GS}=0\text{ V}$, $T_J=25^{\circ}\text{C}$)		V_{SD}	---	---	2.0	V
Diode Reverse Recovery Time Reverse Recovery Charge	$T_J=150^{\circ}\text{C}$ $I_F=\text{rated } I_D$ $di/dt=100\text{ A}/\mu\text{sec}$	t_{rr} Q_{RR}	---	450 3.0	---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{GS}=0\text{ Volts}$ $V_{DS}=25\text{ Volts}$ $f=1\text{ MHz}$	C_{iss} C_{oss} C_{rss}	---	600 250 80	800 450 150	pF

SAFE OPERATING AREA (S.O.A.)
 $T_C = 25^{\circ}\text{C}$, D.C. CONDITION

